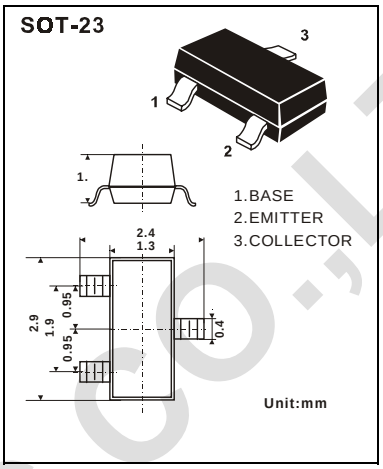
NPN EPITAXIAL SILICON TRANSISTOR

AMPLIFIER TANSISTOR

High Collector-Emitter Voltage:Vcbo=60V

* Collector Current: Ic=500mA
* Collector Dissipation: Pc=225mW(Ta=25℃



ABSOLUTE MAXIMUM RATINGS at Ta=25℃

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	Vcbo	60	V
Collector-Emitter Voltage	Vceo	60	V
Emitter-Base Voltage	Vebo	4	V
Collector Current	Ic	500	mA
Collector Dissipation Ta=25℃*	P_D	225	mW
Junction Temperature	Tj	150	℃
Storage Temperature	Tstg	-55-150	℃

ELECTRICAL CHARACTERISTICS at Ta=25℃

Characteristic	Symbol	Min	Typ	Max	Unit	Test Conditions
Collector-Base Breakdown Voltage	BVcbo	60			V	Ic=100uA Ie=0
Collector-Emitter Breakdown Voltage#	BVceo	60			V	Ic= 1mA Ib=0
Emitter-Base Breakdown Voltage	BVebo	4			V	Ie= 100uA Ic=0
Collector Cutoff Current	Icbo			100	nA	Vcb= 60V Ie=0
Collector Cutoff Current	Ices			100	nA	Vce= 60V Ib= 0
DC Current Gain	Hfe_1	80		250		Vce=1V Ic=10mA
DC Current Gain	Hfe_2	80				Vce=1V Ic=100mA
Collector-Emitter Saturation Voltage	Vce(sat)			0.25	V	Ic=100mA Ib=10mA
Base-Emitter On Voltage	Vbe(on)			1.2	V	Ic=100mA Vce=1V
Current Gain-Bandwidth Product	f_T		100		MHz	Vce=2V Ic=10mA
						f=100MHz

* Total Device Dissipation : FR=1x0.75x0.062in Board,Derate 25℃.

Pulse Test : Pulse Width ≤300uS,Duty cycle ≤2%

DEVICE MARKING: MMBTA05LT1=1H